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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/775,106	02/01/2001	Gerard A. Mourou	30275/939A	4544
4743 7590 01/30/2008 MARSHALL, GERSTEIN & BORUN LLP 233 S. WACKER DRIVE, SUITE 6300 SEARS TOWER CHICAGO, IL 60606			EXAMINER	
			EVANS, GEOFFREY S	
			ART UNIT	PAPER NUMBER
,			1793	
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Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

		Application No.	Applicant(s)			
Office Action Summary		09/775,106	MOUROU ET AL.			
		Examiner	Art Unit			
		Geoffrey S. Evans	1793			
	The MAILING DATE of this communication appears on the cover sheet with the correspondence address Period for Reply					
A SHOF WHICH - Extensic after SIX - If NO pe - Failure t Any repl	RTENED STATUTORY PERIOD FOR REPLY EVER IS LONGER, FROM THE MAILING DA ons of time may be available under the provisions of 37 CFR 1.13 (6) MONTHS from the mailing date of this communication. Friod for reply is specified above, the maximum statutory period we or reply within the set or extended period for reply will, by statute, by received by the Office later than three months after the mailing opatent term adjustment. See 37 CFR 1.704(b).	ATE OF THIS COMMUNICATION 36(a). In no event, however, may a reply be tim will apply and will expire SIX (6) MONTHS from a cause the application to become ABANDONE	N. nely filed the mailing date of this communication. D (35 U.S.C. § 133).			
Status						
1)⊠ R	esponsive to communication(s) filed on 30 O	<u>ctober 2007</u> .				
·=	This action is FINAL . 2b)⊠ This action is non-final.					
•	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is					
closed in accordance with the practice under Ex parte Quayle, 1935 C.D. 11, 453 O.G. 213.						
Disposition	n of Claims					
4a 5)□ C 6)図 C 7)□ C	laim(s) <u>46-105</u> is/are pending in the application) Of the above claim(s) is/are withdraw laim(s) is/are allowed. laim(s) <u>46-105</u> is/are rejected. laim(s) is/are objected to. laim(s) are subject to restriction and/or	vn from consideration.	,			
Application	n Papers					
10)□ Th Al R	ne specification is objected to by the Examine ne drawing(s) filed on is/are: a) accepplicant may not request that any objection to the eplacement drawing sheet(s) including the correct ne oath or declaration is objected to by the Ex	epted or b) objected to by the I drawing(s) be held in abeyance. See ion is required if the drawing(s) is ob	e 37 CFR 1.85(a). jected to. See 37 CFR 1.121(d).			
Priority un	der 35 U.S.C. § 119					
 12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) All b) Some * c) None of: Certified copies of the priority documents have been received. Certified copies of the priority documents have been received in Application No Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received. 						
Attachment/-	1	•				
Attachment(s 1) Notice of) of References Cited (PTO-892)	4) Interview Summary	(PTO-413)			
2) Notice of 3) Information	of Draftsperson's Patent Drawing Review (PTO-948) tion Disclosure Statement(s) (PTO/SB/08) lo(s)/Mail Date 20071030.	Paper No(s)/Mail Do 5) Notice of Informal P 6) Other:	ate			

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DETAILED ACTION

- 1. This office action is in response to the filing of a request for continued examination (RCE) of 30 October 2007.
- 2. The reissue oath/declaration filed with this application is defective (see 37 CFR 1.175 and MPEP § 1414) because of the following: The reissue oath/declaration filed with this application is defective because it fails to identify at least one error which is relied upon to support the reissue application. See 37 CFR 1.175(a)(1) and MPEP Section 1414. Applicant has submitted copies of the reissue declaration from the parent reissue application. This declaration is no longer applicable to the errors that are being corrected in this divisional. While the specific errors listed were corrected in the divisional, other errors are now being addressed in this application. Applicant needs to specify the errors that are now being corrected. In accordance with 37 CFR 1.175(b)(1), a supplemental reissue oath/declaration under 37 CFR 1.175(b)(1) must be received before this reissue application can be allowed.
- 3. Claims 46-78, 80, 81-105 are rejected under 35 U.S.C. 112, first paragraph, as failing to comply with the enablement requirement. The claim(s) contains subject matter which was not described in the specification in such a way as to enable one skilled in the art to which it pertains, or with which it is most nearly connected, to make and/or use the invention. There is no disclosure of the entire genus of non-biological material or opaque non-biological material but only a few examples of non-biological material.

 Enablement of a few species in a large genus does not enable the entire genus in an art area that is unpredictable. Regarding claim 53, there is no disclosure of the genus of

materials with two layers and laser induced breakdown substantially affects one layer and not the other layer. Additionally there is no disclosure of an embodiment with a beam scanned underneath the material as recited in claims 81,86,91 and 96.

- 4. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 5. This application currently names joint inventors. In considering patentability of the claims under 35 U.S.C. 103(a), the examiner presumes that the subject matter of the various claims was commonly owned at the time any inventions covered therein were made absent any evidence to the contrary. Applicant is advised of the obligation under 37 CFR 1.56 to point out the inventor and invention dates of each claim that was not commonly owned at the time a later invention was made in order for the examiner to consider the applicability of 35 U.S.C. 103(c) and potential 35 U.S.C. 102(e), (f) or (g) prior art under 35 U.S.C. 103(a).
- 6. Claims 46-52,55,57,58,62 and 63 are rejected under 35 U.S.C. 103(a) as being unpatentable over Sherman et al. in the article "Transient response of metals to ultrashort pulse excitation" in view of Nishikawa et al. in Japan Patent No. 62-144,893. Sherman et al. discloses a laser induced breakdown (LIB) of copper and molybdenum (a non-biologic material) (see page 1115, column 1, line 58 -column 2, line 2 and page116, paragraph 1). Figures 1(a)-(b) of Sherman et al. specifically depicts the change in slope, i.e. no longer proportional to the square root of the pulse width. Page

116, column 1 of Sherman et al. discloses that there are two distinct regions, the short pulse region and the long pulse region. The short pulse region, less than 500 picoseconds, is disclosed as having a damage threshold that is independent of pulse duration. The long pulse regions, greater than 1 nanosecond, are described as having a damage threshold that scales with T1-2 (page 1116, column 1, paragraph1). Additionally, Sherman discloses using pulse durations of 2.5 picoseconds (2500 fs) with pulse energy of 1 mJ (Page 115, column 1, last full paragraph). Sherman et al. specifically states that the short pulse region is independent of the pulse duration and has a higher damage threshold than anticipated and shows use of pulses below the characteristic pulse width (Figure 1 and page 1116, column 1, paragraph 1). Sherman discloses the use of a laser operating in the claimed pulse width region, i.e. at or below the fluence breakdown threshold for the particular material being operated on within the claimed ranges (Figure 1 and page 1116, column 1, paragraph 1). The laser pulses of Sherman et al. must be directed at the workpiece for the workpiece to absorb the energy from the laser pulses and to successfully ablate material. With respect to claim 47, Sherman et al. discloses: using a C02 laser with a wavelength of 9.3 microns and a resolution of 1 micron (see page 1115, column 1, paragraph 6 to column 2, paragraph 2). The resolution has a maximum dimension of 1 micron is less than the size of the wavelength of the laser beam (9.3 microns); the limitations of claim 47 are met. Since Sherman et al. and the instant application are both performing laser induced breakdown processes with similar operating parameters, it is inherent that the breakdown disclosed by Sherman et al. includes changes caused by one or more or ionization, free electron

multiplication, dielectric breakdown, plasma formation, and vaporization. Sherman et al. does not disclose that only part of the beam causes laser ablation, however Sherman et al. discloses that the laser beam is gaussian (see page 1115, column 2,lines 1-6) and that the laser beam is focused. Nishikawa et al. teach that when using a laser beam that has a gaussian shape it will only ablate (evaporate) materials in the center part of the beam with a fluence level over a threshold value (see abstract and figure 1). It would have been obvious to adapt Sherman et al. in view of Nishikawa et al. to provide this to more accurately laser process the workpiece.

7. Claims 46, 48,49,50, 51/46, 51/48, 51/49, 51/50, 55/46,55/48,55/49,55/50, 57/46, 57/48, 57/49, 57/50, 58/46, 58/48, 58/49, 58/50, 62/55/46, 62/55/48,62/55/49, 62/55/50, 63/46,63/48,63/49,63/50,68/46, 68/48,68/49, 68/50, 70/46,70/48,70/49,70/50, 71/46, 71/48,71/49,71/50, 73/46,73/48,73/49,73/50, and 78 are rejected under 35 U.S.C. 102(b) as being anticipated by Schwab et al. in the article "Femtosecond-Excimer Laser Patterning of YBa2Cu307 Films" in view of Nishikawa et al. in Japan Patent document No. 62-144,893. Schwab et al. discloses laser ablation of a non-biologic material (a superconductor) with 500 femtosecond laser pulses with a fluence of 0.2 Joules per square centimeter at the workpiece surface. Since there is no discernible heat effected zone (see figure 2), inherently the wavelength of the laser pulses must be at or equal to the pulse width at which laser induced breakdown becomes essentially accurate at a corresponding fluence. Since Schwab et al. and the instant application are both performing laser induced breakdown processes with similar operating parameters, it is inherent that the breakdown disclosed by Sherman et al. includes changes caused by

one or more or ionization, free electron multiplication, dielectric breakdown, plasma formation, and vaporization. Schwab et al. does not disclose configuring the laser beam such that a first area within a spot size of the beam exceeds a breakdown threshold and such that a second area within the spot size does not exceed the breakdown threshold. Nishikawa et al. teach using a lens to configure the beam such that a first area within a spot size of the beam exceeds a breakdown threshold and such that a second area within the spot size does not exceed the breakdown threshold (see figure 1). It would have been obvious to adapt Schwab et al. in view of Nishikawa et al. to provide this to more accurately laser process the workpiece.

8. Claims 46,48-50,51/46,51/48,51/49, 51/50,52/46,52/48,52/49, 52/50, 55/46, 55/48, 55/49,55/50,57/46,57148,57/49,57150,58/57146,58157148,58157149,58/57150, 62/46,62/48,62/49,62/50,63/46,63/48,63/49,63/50, 65/46,65/48,65/49,65/50, 68/46, 68/48, 68/49,68/50,69/46,69/48,69/49,69/50,71/46,71/48,71/49,71/50,72/46,72/50, 73/46,73/48,73/49,73/50, and 78 are rejected under 35 U.S.C. 102(e) as being anticipated by Alexander in U.S. Patent No. 6,489,589 B1 in view of Nishikawa et al. in Japan Patent document No. 62-144,893. Alexander discloses (see column 9;line 63 to column 10,line 38)laser machining stainless steel, gold, copper, iron, nickel, titanium, silicon, and diamond, which is far less than a pulse width of 10 picoseconds which is disclosed by the instant application as the point at which machining is essentially accurate with these materials. Since Alexander discloses a pulse width shorter than 10 picoseconds inherently under Applicant's discovered law of nature (the log-log relationship between the fluence threshold at which breakdown occurs versus laser

pulse width, the relationship exhibiting a distinct change in slope with respect to decreasing pulse width to a nearly constant value) the laser pulse ablation of Alexander must also be subject to the same law of nature. See EMI Group North America v. Cypress Semiconductor Corp., 60 USPAQ 1423,1430 (CAFC 2001), which states "Recitation of a law of nature does not distinguish a claim from prior art. Funk Bros. Seed Co. vs. Kalo Inoculatn Co., 333 U.S. 127,130 (1948) ("[M]anifestations of laws of nature {are} free to all men and reserved exclusively to none. He who discovers a hitherto unknown phenomenon of nature has no claim to monopoly of it which the law recognizes.")'. Similarly Alexander's pulse width must be below the pulse width at which the laser induced breakdown becomes essentially accurate and the point at which the size of the feature is not limited by thermal diffusion and the pulse width of Alexander is sufficiently short that the affected area is substantially determined solely by the beam shape and fluence in relation to the threshold for laser induced breakdown. Alexander does not disclose configuring the laser beam such that a first area within a spot size of the beam exceeds a breakdown threshold and such that a second area within the spot size does not exceed the breakdown threshold. Nishikawa et al. teach using a lens to configure the beam such that a first area within a spot size of the beam exceeds a breakdown threshold and such that a second area within the spot size does not exceed the breakdown threshold (see figure 1). It would have been obvious to adapt Alexander in view of Nishikawa et al. to provide this to more accurately laser process the workpiece. Regarding claims 65/46,65/48,65/49,65/50, Alexander discloses in column

10,lines13-14" ... the laser beam may be oscillated to cover a wider area. "which is considered to mean scanning of the laser beam to the workpiece.

- 9. Claims 47, 51/47,52/47,55/47,56,57/47,58/57/47, 59,60,61,62/47,63/47, 65/47,66, 68/47,69/47,70/47,71147,72/47,73/47 are rejected under 35 U.S.C. 103(a) as being unpatentable over Alexander in U.S. Patent No. 6,489,589 B1 in view of Nishikawa et al. in Japan Patent No. 62-144,893 and Lai in U.S. Patent No. 5,984,916. Nishikawa et al. teach using a lens to configure the beam such that a first area withina spot size of the beam exceeds a breakdown threshold and such that a second area within the spotsize does not exceed the breakdown threshold (see figure 1). Lai as shown in figure 5 teaches creating an interaction zone that is smaller than the wavelength of the laser beam beneath the surface of the workpiece. It would have been obvious to adapt Alexander in view of Nishikawa et al. and Lai to provide this to more precisely shape the area being cut by not using the entire beam to laser ablate the workpiece and to create an interaction zone smaller than the wavelength of the laser beam to decrease the size of the part of the material that has material properties change.
- 10. Claims 64/46,64/48,64/49, and 64/50 are rejected under 35 U.S.C. 103(a) as being unpatentable over Alexander in view of Nishikawa et al. as applied to claims 46,48,49, and 50 above, and further in view of Mourou et al. in U.S. Patent No. 5,235,606. Mourou et al. (606) teach generating a short optical pulse by stretching the pulse in time, amplifying the pulse, and recompressing the amplified pulse. It would

have been obvious to adapt Alexander in view of Nishikawa et al. and Mourou et al. to provide this to create a short high peak power pulse for laser machining.

- 11. Claim 64/47 is rejected under 35 U.S.C. 103(a) as being unpatentable over Alexander in view of Nishikawa et al. and Lai as applied to claim 47 above, and further in view of Mourou et al. in U.S. Patent No. 5,235,606. Mourou et al. (606) teach generating a short optical pulse by stretching the pulse in time, amplifying the pulse, and recompressing the amplified pulse. It would have been obvious to adapt Alexander in view of Nishikawa et al., Lai and Mourou et al. to provide this to create a short high peak power pulse.
- 12. Claims 53/52/46, 53/52/48, 53/52/49, 53/52/50, 54/53/52/46, 54/53/52/48, 54/53/52/49, 54/53/52/50, 79, and 80 are rejected under 35 U.S.C. 103(a) as being unpatentable over Alexander in view of Nishikawa et al. as applied to claims 52/46,52/48,52/49,52/50 and further in view of Wojnarowski et al. in U.S. Patent No. 5,104,480. Wojnarowski et al. teaches laser machining gold (see column 7, line 19) above a substrate of glass (see column 6,line 64) to create a conductive pattern for an integrated circuit. It would have been obvious to adapt Alexander in view of Nishikawa et al. and Wojnarowski et al. to provide this to create an integrated-circuit on .the substrate.
- 13. Claims 53/52/47,54/53/52/47, and 68/47 are rejected under 35 U.S.C. 103(a) as being unpatentable over Alexander in view of Nishikawa et al. and Lai as applied to claim 47 above, and further in view of Wojnarowski et al. in U.S. Patent No. 5,104,480. Wojnarowski et al. teaches laser machining gold (see column 7, line 19) above a

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substrate of glass (see column 6,line 64) to create a conductive pattern for an integrated circuit. It would have been obvious to adapt Alexander in view of Nishikawa et al., Lai, and Wojnarowski et al. to provide this to create an integrated circuit on the substrate.

14. Claims 67,74-77,81-105 contain subject matter allowable over the prior art or record, but are rejected as being based upon a defective reissue declaration under 35 U.S.C. 251 as stated in the second paragraph of this office action and are rejected under 35 USC 112, first paragraph as stated in the third paragraph of this office action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Geoffrey S. Evans whose telephone number is (571)-272-1174. The examiner can normally be reached on Mon-Fri 7:00AM to 3:30 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Jonathan Johnson can be reached on (571)-272-1177. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

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Geoffey & Evans Primary Examiner Art Unit 1793

GSE